

01 Oct 2013

Capacitive Properties and Structure of RuO₂-HfO₂ Films Prepared by Thermal Decomposition Method

Xuehua Liu

Junqiu Zhu

Xin Wang

Jinghua Sun

et. al. For a complete list of authors, see https://scholarsmine.mst.edu/matsci_eng_facwork/1957

Follow this and additional works at: https://scholarsmine.mst.edu/matsci_eng_facwork

 Part of the [Materials Science and Engineering Commons](#)

Recommended Citation

X. Liu et al., "Capacitive Properties and Structure of RuO₂-HfO₂ Films Prepared by Thermal Decomposition Method," *Physics Procedia*, vol. 50, pp. 416-420, Elsevier BV, Oct 2013.

The definitive version is available at <https://doi.org/10.1016/j.phpro.2013.11.064>

This Article - Conference proceedings is brought to you for free and open access by Scholars' Mine. It has been accepted for inclusion in Materials Science and Engineering Faculty Research & Creative Works by an authorized administrator of Scholars' Mine. This work is protected by U. S. Copyright Law. Unauthorized use including reproduction for redistribution requires the permission of the copyright holder. For more information, please contact scholarsmine@mst.edu.

International Federation for Heat Treatment and Surface Engineering 20th Congress
Beijing, China, 23-25 October 2012

Capacitive Properties and Structure of RuO₂-HfO₂ Films Prepared by Thermal Decomposition Method

Xuehua Liu^a, Junqiu Zhu^a, Xin Wang^a, —, Junmei Sun^a, Zhongzhi Tang^b, Teng Zhang^b,
Matthew J. O'Keefe^c, Dian Tang^b

^aCollege of Materials Science and Engineering, Fuzhou University, Fuzhou and 350108, China

^bInstitute for Materials Research, Fuzhou University, Fuzhou and 350108, China

^cMaterials Research Center, Missouri University of Science and Technology, USA

Abstract

Binary RuO₂-HfO₂ films on Ti substrates were prepared by a thermal decomposition method. cyclic voltammetric and charge/discharge properties of the RuO₂-HfO₂ electrodes were characterized. It was determined that the incorporation of HfO₂ into RuO₂ greatly improved the capacitive properties of the material. The RuO₂-HfO₂ electrodes showed excellent cyclic stability, with no decay in charge capability during 1000 CV cycles in acidic solution. A nominal content of 50 mol% RuO₂ and 50 mol% HfO₂ gave the highest specific capacitance of 789.3 F/g (RuO₂). The excellent capacitive properties and stability were related to the hydrous amorphous mixed-oxides formed in the film. This work proves that high capacitive performance of RuO₂-based electrode materials can be obtained by thermal decomposition, even with the retained chloride in the film.

© 2013 The Authors. Published by Elsevier B.V. Open access under [CC BY-NC-ND license](#).

Selection and peer-review under responsibility of the Chinese Heat Treatment Society

Keywords: RuO₂-HfO₂; film; supercapacitor; thermal decomposition method;

1. Introduction

Metal oxides are promising candidates for supercapacitor electrodes Simon et al. (2008) or Lokhande et al (2011) or Aricò et al (2005). In recent years, RuO₂ has been widely studied due to its good electrochemical reversibility,

* Corresponding author. Tel.: +086-0591-22866540; fax: +086-0591-22866537.

E-mail address: xinxinwx@fzu.edu.cn

highest specific capacitance, and long cycle life in H_2SO_4 . Electrochemical capacitors based on hydrous ruthenium oxide are known to achieve excellent specific capacitances, higher than 720 F/g Yuan et al. (2012). Some preparation methods, including chemical synthesis, sol-gel, and electrochemical deposition, have achieved high capacitance Patake et al (2008) or Chang et al (2009) or Patake et al (2010), but could not be applied to industrial production. In addition, despite the excellent performance of hydrous RuO_2 electrodes, their high material cost limits their widespread use in industry. Mixing RuO_2 with other oxides, including Ta_2O_5 Zheng et al (1995), Cr_2O_3 , Chen et al (2011), and TiO_2 Bo et al (2006), has been considered a most effective way to reduce the cost. Thus, selection of other potential metal oxides and suitable preparation methods are essential to achieve the requirements for supercapacitors. The thermal decomposition method (TDM) is the easiest technique for obtaining mixed-oxide electrodes, but is not employed in preparing hydrous RuO_2 due to chlorine contamination Kurzweil et al (2009) or Chang et al (2006). Our exploratory work on $\text{RuO}_2\text{-SnO}_2$ has suggested that a very high specific capacitance can be achieved by a low-temperature sintering TDM Wang et al (2011). In this paper, $\text{RuO}_2/\text{HfO}_2$ oxides were deposited on Ti by TDM. Study of Ru/Hf molar ratio effects on $\text{RuO}_2\text{-HfO}_2$ electrode structure, capacitive properties, and stability will be conducted.

Nomenclature

$C_{\text{S,RuO}_2}$ specific capacitance

2. Experimental

The details of TDM have been described elsewhere Wang et al (2007). 2 mm-thick industrial titanium (TA2) plates were degreased, polished, etched in 10 wt.% boiling oxalic acid for 1 h, ultrasonically cleaned, and then dried. The precursors RuCl_3 and HfCl_4 were separately dissolved in anhydrous ethanol and then homogeneously mixed. The Ru-loading in the films was 0.8 mg/cm^2 while that of HfO_2 was varied from 0 (pure RuO_2) to 100 mol% (pure HfO_2) in 10 mol% increments. The solutions were then brushed on the pretreated Ti and thermally decomposed at 300°C in air for 1 h. Samples were labeled by HfO_2 content.

The electrochemical properties of the $\text{RuO}_2\text{-HfO}_2$ electrodes were characterized by cyclic voltammetric and charge/discharge tests in 0.5 M H_2SO_4 solution. The phase structures of the electrodes were examined using X-ray diffraction (XRD) (Philips X pert-MPD), X-ray photoelectron spectroscopy (XPS) (ESCALAB 250, Thermo Fisher Scientific, UK) and field emission high resolution transmission electron microscopy (TEM) (JEM-2010, JEOL Inc., Japan).

3. Results and Discussion

Cyclic voltammetry (CV) curves of the $\text{Ti/RuO}_2\text{-HfO}_2$ electrodes are presented in Figure 1. That of the pure RuO_2 sample (0 %) shows a tail-like peak below 0.1 V (versus SCE, the same hereafter), which is the reported Ru(II)/Ru(III) transition between 0.0 – 0.2 V and reveals some chloride impurities in the sample Kurzweil et al (2009) or Chang et al (2006). This chlorine contamination not only caused the CV curve asymmetry but also decreased the voltammetric charge. So, thermal preparation of RuO_2 from chlorides is generally not recommended.

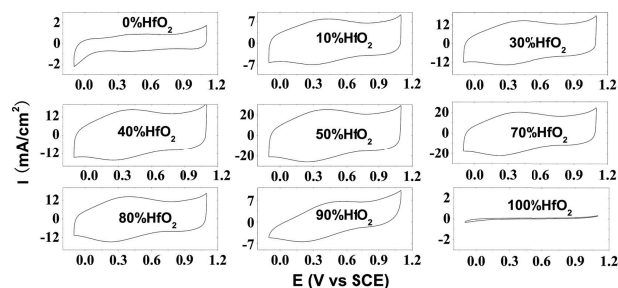


Fig. 1. Voltammetric curves of Ti/RuO₂-HfO₂ electrodes with different mol% HfO₂, at 25 mA/cm² in a 0.5 mol/L H₂SO₄ solution

Only nominal 10mol % HfO₂ content greatly enhanced the CV area, and the peak below 0.1 V vanished. This demonstrated that the Ru(II)/Ru(III) reaction was suppressed by adding a small amount of HfO₂ in the film, which clearly erased the chloride harmful effects on the electrodes. CV curves of samples with HfO₂ between 10 and 80 mol% were symmetrical and showed distinctive redox peaks, indicating that the active materials on the electrodes were highly reversible and thus suitable for use in supercapacitors. The voltammetric area first increased and then decreased with increasing HfO₂. The 50 mol% HfO₂ sample had the largest voltammetric area. The 90 mol% HfO₂ sample had a small and asymmetrical CV curve, revealing its inferior capacitive features. The pure HfO₂ film had almost no voltammetric response current due to HfO₂ being an inert oxide.

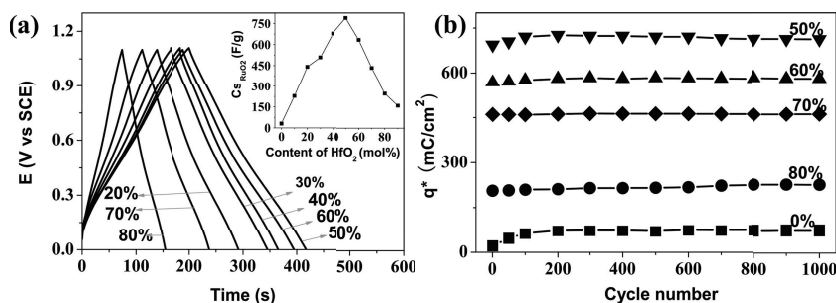


Fig. 2. Charge-discharge curves and specific capacitance, C_{S,RuO_2} (inserted in Fig. 2a) (a) and the C_{S,RuO_2} vs. CV cycle numbers (b) of the RuO₂-HfO₂ electrodes with different mol% HfO₂. Charge/discharge current density of 5 mA/cm², CV scan rate of 50 mV/s, 0.5 mol/L H₂SO₄ solution.

Selected Ti/RuO₂-HfO₂ charge-discharge curves, measured in 0.5 mol/L H₂SO₄ at 5 mA/cm², are shown in Figure 2(a). Their triangular shapes indicate RuO₂-containing materials. The specific capacitance, C_{S,RuO_2} , of the samples was calculated from the inset discharge curves. It is apparent that C_{S,RuO_2} was influenced greatly by HfO₂ content in the films. The pure RuO₂ C_{S,RuO_2} was as low as 30.6 F g⁻¹, which is in agreement with that reported for pure RuO₂ (around 50 F g⁻¹) synthesized by TDM [11]. The C_{S,HfO_2} of 1.96 F g⁻¹ of the pure HfO₂ sample indicated that this oxide was very inactive Zhang et al (2007). However, the highest specific capacitance of 789.3 F/g was measured for 50 mol% HfO₂ film, approximately 25 times higher than that of the prepared pure RuO₂. The volcano-like charge-composition peaks, also reported in some systems Rosario et al (2009) or Doubova et al (2002) or Wong et al (2004), imply synergistic effects in these binary oxides.

Figure 2b shows the samples stability in acid, evaluated by CV at a scanning rate of 50 mV/s, and indicates the prepared electrodes were stable in acid even after 1000 cycles. A slight increase in q^* , anodic voltammetric charge, after the first 100 cycles may have been due to gradual wetting on/in these binary oxides and depended on their internal porosity.

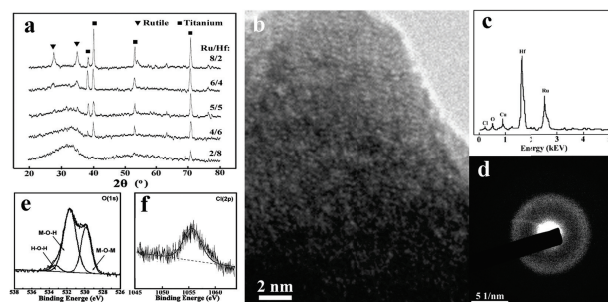


Fig. 3. XRD patterns (a), HRTEM image (b), EDX image (c), XPS spectra of O1s (d) and Cl(2p) (e), and SEAD pattern (f) for Ti/RuO₂-HfO₂ electrode with 50 mol% HfO₂

Figure 3a shows the XRD patterns of selected samples. For Ru-rich samples, peaks at 2θ from 28.0 to 35.5°, were assigned to rutile RuO₂. For Hf-rich samples, wide humps suggest the films were mainly amorphous. For further study of these amorphous structures, the morphology of the 50 mol% HfO₂ sample was observed by high-resolution transmission electron microscopy (HRTEM). The images (Fig. 3b) did not show any long-ranged arrangement, along with the SAED patterns (Fig. 3f), which clearly indicated the amorphous nature of the films. The molar ratio of Ru/Hf by EDX (Fig. 3c) was in accordance with that of the precursors. Residual chlorine was as expected, because above 400 °C, the chloride precursors used are completely decomposed [17].

The XPS spectrum of the 50 mol% HfO₂ film is shown in Figs. 3e and 3f. The O(1s) spectrum was deconvoluted into three parts (Fig. 3d); bridged oxygen (M–O–M) with binding energy at 529.8 eV, hydroxide (M–O–H) at 531.9 eV, and molecular water (H–O–H) at 533.4 eV, which are in accordance with published data for hydrous RuO₂ Da Silva et al (2000), and indicate that this film was mainly hydrated RuO₂. The peak at 1055.2 eV (Fig. 3e) was assigned to Cl(2p), present because of the retained chloride in the film.

4. Conclusions

The present thermal decomposition method was proved to be useful to prepare RuO₂-based oxide coated electrode materials for supercapacitors. The 50%RuO₂+50%HfO₂ electrode prepared this way not only achieved a specific capacitance value of ca. 790 F/g but also overcame the negative effects of chloride. The thermal decomposition method allows preparation of these mixed oxides on the large-scale.

Acknowledgements

The authors gratefully acknowledge the financial support of the National High Technology Research and Development Projects (863) of China (2007AA03Z325), Natural Science Foundation of China (11104031), the International Cooperation Projects of Fujian Province (2007I004), and Natural Science Foundation of Fujian Province (2013J01175).

References

- Simon, P., Gogotsi, Y., 2008. Materials for electrochemical capacitors. *Nat. Mater.* 7, 845–854.
- Lokhande, C.D., Dubal, D.P., Joo, O.S., 2011. Metal oxide thin film based supercapacitors. *Curr. Appl. Phys.* 11, 255–270.
- Aricò, A.S., Bruce, P., Scrosati, B., Tarascon, J.M., van, S.W., 2005. Nano-structured materials for advanced energy conversion and storage devices. *Nat. Mater.* 4, 366–377.
- Yuan, Y.F., Pei, Y.B., Guo, S.Y., Fang, J., Yang, J.L., 2012. Sparse MnO₂ nanowires clusters for high-performance supercapacitors. *Mater. Lett.* 73, 194–197.

- Patake, V.D., Lokhande, C.D., 2008. Chemical synthesis of nano-porous ruthenium oxide (RuO_2) thin films for supercapacitor application. *Appl. Surf. Sci.* 254, 2820–2824.
- Chang, K.H., Hu, C.C., Chou, C.Y., 2009. Textural and pseudocapacitive characteristics of sol–gel derived $\text{RuO}_2 \cdot x\text{H}_2\text{O}$: hydrothermal annealing vs. annealing in air. *Electrochimica Acta* 54, 978–983.
- Patake, V.D., Pawar, S.M., Shinde, V.R., Gujar, T.P., Lokhande, C.D., 2010. The growth mechanism and supercapacitor study of anodically deposited amorphous ruthenium oxide films. *Curr. Appl. Phys.* 10, 99–103.
- Zheng, J.P., Cygan, P.J., Jow, T.R., 1995. Hydrous Ruthenium Oxide as an Electrode Material for Electrochemical Capacitors. *J. Electrochem. Soc.* 142, 2699–2703.
- Chen, H.R., Lai, H.H., Jow, J.J., 2011. Annealing effect on the performance of $\text{RuO}_2\text{-Ta}_2\text{O}_5/\text{Ti}$ electrodes for use in supercapacitors. *Mater. Chem. Phys.* 125, 652–655.
- Bo, G., Xiao, G.Z., Chang, Z.Y., Juan, L., Long, Y., 2006. Amorphous $\text{Ru}_{1-y}\text{Cr}_y\text{O}_2$ loaded on TiO_2 nanotubes for electrochemical capacitors. *Electrochimica Acta* 52, 1028–1032.
- Kurzweil, P., 2009. Precious metal oxides for electrochemical energy converters: pseudocapacitance and pH dependence of redox processes. *Journal of Power Sources* 190, 189–200.
- Chang, K.H., Hu, C.C., 2006. Hydrothermal synthesis of binary Ru–Ti oxides with excellent performances for supercapacitors. *Electrochimica Acta* 52, 1749–1757.
- Wang, X., Tang, D., 2011. Thermal decomposition synthesis of binary Ru–Sn oxides and their specific capacitance. *Integrated Ferroelectrics* 128, 183–190.
- Wang, X., Tang, D., Zhou, J.E., 2007. Microstructure, Morphology and electrochemical property of $\text{RuO}_2\text{70SnO}_2\text{30mol\%}$ and $\text{RuO}_2\text{30SnO}_2\text{70mol\%}$ coatings. *Journal of Alloys and Compounds* 430(14), 60–66.
- Zhang, T., Tang, D., Shao, Y., Ke, X., You, S., 2007. Synthesis and characterization of nanoscale $\text{Ce}_x\text{Ru}_{(1-x)}\text{O}_2$ coatings with electrochemical activity. *J. Am. Ceram. Soc.* 90, 989–992.
- Rosario, A.V., Bulhões, L.O.S., Pereira, E.C., 2006. Investigation of pseudocapacitive properties of RuO_2 film electrodes prepared by polymeric precursor method. *Journal of Power Sources* 158, 795–800.
- Doubova, L.M., Daolio, S., De Battisti, A., 2002. Examination of RuO_2 single-crystal surfaces: charge storage mechanism in H_2SO_4 aqueous solution. *J. Appl. Electrochem.* 532, 25–23.
- Wong, H., Zhan, N., Ng, K.L., Poon, M.C., Kok, C.W., 2004. Interface and oxide traps in high- κ hafnium oxide films. *Thin Solid Films* 462–463, 96–100.
- Da Silva, L.M., Boodts, J.F.C., De Faria L.A., 2000. ‘In situ’ and ‘ex situ’ characterization of the surface properties of the $\text{RuO}_2(x) + \text{Co}_3\text{O}_4(1-x)$ system. *Electrochimica Acta* 45, 2719–2727.